

24/ 46. The method according to claim 43²¹ wherein said second layer is formed of silicon dioxide having a thickness of approximately five thousand Angstroms.

A1 25 47. The method according to claim 43²¹ wherein said step of removing any portions remaining of the second layer is performed prior to forming a fourth layer in the gap. --

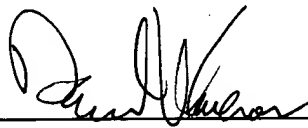
REMARKS

With this continuation application, claims 14-20 of the original application are presented for examination, together with new claims 43-47. These claims are directed towards a method of forming a feature having a selected dimension and are believed patentable in light of all prior art of record. In particular, the method steps carried out by Chau et al. are distinctly different from the method steps as claimed in the present invention. The claimed features are not taught in, or obvious in light of Chau et al. Or other prior art of record. Accordingly, allowance of all claims is respectfully requested.

Respectfully submitted,

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